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an etching stopper film covering an upper surface of the conductor patterns;
a contact hole located in a part of a region between the adjacent conductor patterns and having an end thereof defined by the conductor patterns;
a first insulation film which is filling spaces between said plurality of conductor patterns where the contact hole is not formed and not extending over the etching stopper film; and
a sidewall insulation film formed on an inner wall of the contact hole so that side walls of the conductor pattern and the etching stopper film are covered.

9. (Four Times Amended) A semiconductor device comprising:
a semiconductor substrate;
a plurality of word lines formed over the semiconductor substrate and extended in a first direction;
an etching stopper film covering upper surfaces of the word lines;
a first insulation film formed over the etching stopper film and the semiconductor substrate;
an opening, located between the word lines, reaching the semiconductor substrate through the first insulation film;
a first sidewall insulation film, formed in the opening, covering a side wall of the first insulation film;
a second sidewall insulation film, formed in the opening, covering side walls of a stacked layer of the word lines and the etching stopper film; and
a contact hole formed in the opening, reaching the semiconductor substrate, the first sidewall

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insulation film and the second sidewall insulation film defining an end of the contact hole, the contact hole having a first width ends of which are defined by the first sidewall insulation film and a second width ends of which are defined by the second sidewall insulation film,

the first width being larger than a space between the adjacent word lines and the second width being substantially the same as a width subtracted twice a width of the second sidewall insulation film from the space between the adjacent word lines.

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11. (Four Times Amended)

A semiconductor device comprising:

a semiconductor substrate;

a plurality of word lines formed over the semiconductor substrate and extended in a first direction;

a first insulation film formed over the word lines and the semiconductor substrate;

a plurality of bit lines formed over the first insulation film and extended in a second direction;

an etching stopper film covering upper surfaces of the bit lines;

a second insulation film formed over the etching stopper film and the first insulation film;

an opening, located between the adjacent bit lines;

a first sidewall insulation film, formed in the opening, covering a side wall of the second insulation film;

a second sidewall insulation film, formed in the opening, covering side walls of a stacked layer of the bit lines and the etching stopper film;

a contact hole formed in the opening, reaching the semiconductor substrate, the first sidewall insulation film and the second sidewall insulation film defining an end of the contact hole, the contact hole having a first width ends of which are defined by the first sidewall insulation film and a second width ends of which are defined by the second sidewall insulation film; and

a capacitor having one electrode connected to the semiconductor substrate through the contact hole,

the first width being larger than a space between the adjacent bit lines and the second width being substantially the same as a width subtracted twice a width of the second sidewall insulation film from the space between the adjacent bit lines.

12. (Four Times Amended) A semiconductor device comprising:

a semiconductor substrate;

a plurality of word lines formed over the semiconductor substrate and extended in a first direction;

a first insulation film formed over the word lines and the semiconductor substrate;

a plurality of bit lines formed over the first insulation film and extended in a second direction;

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an etching stopper film covering upper surfaces of the bit lines;
a contact hole located in a part of a region between the adjacent bit lines, having ends thereof defined by the bit lines;
a second insulation film which is filling spaces between said plurality of bit lines where the contact hole is not formed and not extending over the etching stopper film;
a sidewall insulation film, formed in the contact hole, covering a side wall of the second insulation film, side walls of the bit lines and side walls of the etching stopper film; and
a capacitor having one electrode connected to the semiconductor substrate through the contact hole.

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37. (Twice Amended) A semiconductor device comprising:
a base substrate;
a first conducting film formed over the base substrate and including two conductor patterns adjacent to each other;
an etching stopper film covering each upper surface of the two conductor patterns;
a first insulation film formed over the etching stopper film and the base substrate;
an opening, located between the two conductor patterns, reaching the base substrate through the first insulation film;
a first sidewall insulation film, formed in the opening covering a side wall of the first insulation film ;
a second sidewall insulation film, formed in the opening covering an each side wall of a

AMENDMENT

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stacked layer of the two conductor patterns and the etching stopper film ; and

a contact hole formed in the opening, reaching the base substrate, the first sidewall insulation film and the second sidewall insulation film defining an end of the contact hole, the contact hole having a first width ends of which are defined by the second sidewall insulation film and a second width ends of which are defined by the first sidewall insulation film,

the first width being larger than a space between the two conductor patterns and the second width being substantially the same as a width subtracted twice a width of the sidewall insulation film from the space between the two conductor patterns.
